Errata

Erratum: Theoretical investigation of the pressure dependences of energy gaps in semiconductors [Phys. Rev. B 32, 1152 (1985)]

Seongbok Lee, J. Sanchez-Dehesa, and John D. Dow

We regret that our paper fails to acknowledge the earlier work of Verges, Glötzel, Cardona, and Andersen[1] and Chang, Froyen, and Cohen,[2] in which pressure dependences of band gaps of the common semiconductors were reported. Those theoretical calculations were based on different formulations of local density theory from our own, but nevertheless reached conclusions and obtained numerical results that, while different in detail, were generally similar to our own and to other recent theories.[3] We also point out that there have been a number of local density calculations[4] for pressure-dependent electronic structures of materials other than the common semiconductors discussed in our paper.

We thank Professor M. Cardona, Professor M. Cohen, and Professor S. Trickey for calling their work to our attention.

[1]J. A. Verges, D. Glötzel, M. Cardona, and O. K. Andersen, Phys. Status Solidi (b) **113**, 519 (1979).

[2]K. J. Chang, S. Froyen, and M. L. Cohen, Solid State Commun. **50**, 105 (1984).

[3]See also the recent results by M. Hanfland, K. Syassen, and N. E. Christensen, J. Phys. (Paris) Colloq. **45**, C8-57 (1984); N. E. Christensen, Phys. Rev. B **30**, 5753 (1984).

[4]See, for example, S. B. Trickey, A. K. Ray, and J. P. Worth, Phys. Status Solidi (b) **106**, 613 (1981); S. Ves, D. Glötzel, M. Cardona, and H. Overhof, Phys. Rev. B **24**, 3073 (1981); N. E. Christiansen, Phys. Status Solidi (b) **123**, 281 (1984); **125**, K59 (1984); A. K. Ray, S. B. Trickey, and A. B. Kunz, *ibid.* **121**, K47 (1984); J. von Boehm and H. Isomaki, J. Phys. C **13**, 4953 (1980); A. Zunger and M. L. Cohen, Phys. Rev. B **20**, 1189 (1979); H. Isomaki and J. von Boehm, Solid State Commun. **34**, 709 (1980); H. Isomaki, J. von Boehm, P. Krusius, and T. Stubb, Phys. Rev. B **22**, 2945 (1980); M. Schreiber and W. Schafer, *ibid.* **29**, 2246 (1984), and references therein.

Erratum: Band offsets from two special GaAs-$Al_xGa_{1-x}As$ quantum-well structures [Phys. Rev. B 32, 5443 (1985)]

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We regret that our paper fails to acknowledge the independent work of Meynadier *et al.*[1] in which excitation spectra of symmetric and asymmetric "two-stepped wells" (separate confinement heterostructures) were utilized to determine conduction- and valence-band offsets in the ratio of 59:41. This ratio is in perfect agreement with the present results for symmetric two-stepped wells.

[1]M. H. Meynadier, C. Delalande, G. Bastard, M. Voos, F. Alexandre, and J. L. Liévin. Phys. Rev. B **31**, 5539 (1985).

Erratum: Incompressible states of the fractionally quantized Hall effect in the presence of impurities: A finite-size study [Phys. Rev. B 32, 6924 (1985)]

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Page 6927, column 2, line 1: "interactions" should read "impurity potential." Also, Ref. 10 should read as follows: When projected onto the lowest Landau level, the original impurity potential $V(r)$ is described by a set of pseudopotential coefficients $\{V_m\}$ which are the potential energies of a particle orbiting the rotationally invariant impurity with orbital angular momentum m.

